

## MAGNETIC MEMORY CELL WITH PLURAL READ TRANSISTORS

### ABSTRACT

A magnetic random access memory (MRAM) device has increased  $\Delta R/R$  for sensing a state of a pin-dependent tunneling (SDT) device. The MRAM device includes plural transistors connected to a read line for sensing the state of the SDT device. Plural transistors lower an underlying resistance during reading, increasing  $\Delta R/R$ . The plural transistors can share a source region.